

L Number	Hits	Search Text	DB	Time stamp
2	4191	(372/43-50).CCLS.	USPAT	2003/08/14 13:03
3	2807	(372/49,9,50,108,101).CCLS.	USPAT	2003/08/14 13:03
5	1172	((372/49,9,50,108,101).CCLS.) and lens	USPAT	2003/08/14 13:04
4	881	((372/43-50).CCLS.) and lens	USPAT	2003/08/14 14:13
6	7	5966399.URPN.	USPAT	2003/08/14 13:50
7	2	("5426657" "5838715").PN.	USPAT	2003/08/14 13:51
8	7	5553089.URPN.	USPAT	2003/08/14 14:03
9	3	("5081639" "5086431" "5212706").PN.	USPAT	2003/08/14 14:03
10	655	((372/49,9,50,108,101).CCLS.) and lens) not (((372/43-50).CCLS.) and lens)	USPAT	2003/08/14 14:25
11	2483	372/43-50.ccls. and (ridge stripe mesa)	USPAT	2003/08/14 14:25
12	486	(372/43-50.ccls. and (ridge stripe mesa)) and lens	USPAT	2003/08/14 14:26
13	0	((372/43-50.ccls. and (ridge stripe mesa)) and lens) not (((372/43-50).CCLS.) and lens) (((372/49,9,50,108,101).CCLS.) and lens))	USPAT	2003/08/14 14:30
14	1	6167070.pn.	USPAT	2003/08/14 14:31
15	1	6037189.pn.	USPAT	2003/08/14 15:02
16	1205	(372/43-50.ccls. and (ridge stripe mesa)) and (film passivation)	USPAT	2003/08/14 15:04
17	1165	372/46.ccls. and (stripe ridge)	USPAT	2003/08/14 15:04
18	666	(372/46.ccls. and (stripe ridge)) and (film passivation)	USPAT	2003/08/14 15:06
19	50	(372/46.ccls. and (stripe ridge)) and (passivation)	USPAT	2003/08/14 15:26
20	9	(372/46.ccls. and (stripe ridge)) and (SiO TiO) near3 (layer film)	USPAT	2003/08/14 15:26
21	26	(US-6463087-\$ or US-6134368-\$ or US-6374028-\$ or US-6455342-\$ or US-6327288-\$ or US-6034983-\$ or US-6219366-\$ or US-6465269-\$ or US-5790578-\$ or US-5665985-\$ or US-6586776-\$ or US-6167070-\$ or US-6122417-\$ or US-6058125-\$ or US-6037189-\$ or US-5970081-\$ or US-5966399-\$ or US-5835517-\$ or US-5553089-\$ or US-5428227-\$ or US-5457569-\$ or US-6472691-\$ or US-5659565-\$ or US-5640410-\$ or US-5333141-\$ or US-4813054-\$).did.	USPAT	2003/08/14 15:52

L Number	Hits	Search Text	DB	Time stamp
1	4405	(semiconductor near3 laser) same (stripe ridge mesa)	USPAT; EPO; JPO; IBM_TDB	2003/08/12 15:27
2	2371	((semiconductor near3 laser) same (stripe ridge mesa)) and 372/\$.ccls.	USPAT; EPO; JPO; IBM_TDB	2003/08/12 17:27
3	112	((((semiconductor near3 laser) same (stripe ridge mesa)) and 372/\$.ccls.) and edge near2 emit\$4	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:44
4	7	6324326.URPN.	USPAT	2003/08/12 18:20
5	18	("4161944" "4179187" "4212660" "4705351" "4886538" "4901324" "4941726" "5119460" "5166940" "5265177" "5422897" "5455879" "5530710" "5659644" "5710789" "5774484" "5864644" "5940557").PN.	USPAT	2003/08/12 18:22
6	4	6134368.URPN.	USPAT	2003/08/12 18:31
7	4	("5284791" "5360763" "5382543" "5717710").PN.	USPAT	2003/08/12 18:33
8	2	nichia.as. and (edge with emit\$4) and laser	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:46
9	212	nichia.as. and laser	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:46
10	70	(nichia.as. and laser) and (ridge stripe)	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:50
11	11910	372/43-50.ccls.	USPAT; EPO; JPO; IBM_TDB	2003/08/12 19:18
12	665	372/43-50.ccls. and (edge with emit\$5)	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:50
13	281	(372/43-50.ccls. and (edge with emit\$5)) and (ridge stripe)	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:50
14	192	((372/43-50.ccls. and (edge with emit\$5)) and (ridge stripe)) not (((semiconductor near3 laser) same (stripe ridge mesa)) and 372/\$.ccls.) and edge near2 emit\$4)	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:51
15	80	((((372/43-50.ccls. and (edge with emit\$5)) and (ridge stripe)) not (((semiconductor near3 laser) same (stripe ridge mesa)) and 372/\$.ccls.) and edge near2 emit\$4)) and (film "Si0.sub.2" "TiO" "SiO")	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:52
16	1	((((372/43-50.ccls. and (edge with emit\$5)) and (ridge stripe)) not (((semiconductor near3 laser) same (stripe ridge mesa)) and 372/\$.ccls.) and edge near2 emit\$4)) and (shad\$4 with film)	USPAT; EPO; JPO; IBM_TDB	2003/08/12 18:52
17	5	6034983.URPN.	USPAT	2003/08/12 19:01
18	13	("5011550" "5079184" "5130269" "5227328" "5229319" "5266127" "5300186" "5399522" "5424243" "5574289" "5657338" "5787106" "5790578").PN.	USPAT	2003/08/12 19:03
19	219	372/43-50.ccls. and (edge with emitting) and (stripe ridge) and active and semiconductor and substrate	USPAT; EPO; JPO; IBM_TDB	2003/08/12 19:40
20	2	372/43-50.ccls. and (edge with emitting) and (stripe ridge) and (shad\$3 with film)	USPAT; EPO; JPO; IBM_TDB	2003/08/12 19:48